TOSHIBA Transistor Silicon NPN Epitaxial Type

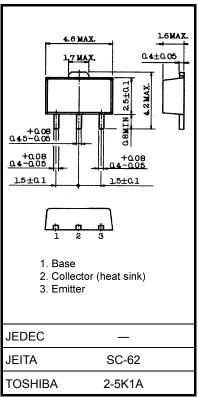
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High-Speed Switching Applications DC-DC Converter Applications Strobe Applications

- High DC current gain: $h_{FE} = 400$ to 1000 (IC = 0.5 A)
- Low collector-emitter saturation voltage: V_{CE} (sat) = 0.15 V (max)
- High-speed switching: t_f = 90 ns (typ.)

| Characteristics | | Symbol | Rating | Unit | |
|-----------------------------|----------|------------------|------------|------|--|
| Collector-base voltage | | V _{CBO} | 40 | V | |
| Collector-emitter voltage | | V _{CEX} | 30 | V | |
| Collector-emitter voltage | | V _{CEO} | 20 | V | |
| Emitter-base voltage | | V _{EBO} | 7 | V | |
| Collector current | DC | Ι _C | 4 | • | |
| | Pulse | I _{CP} | 7 | A | |
| Base current | | Ι _Β | 400 | mA | |
| Collector power dissipation | DC | PC | 1.0 | W | |
| | t = 10 s | (Note 1) | 2.5 | | |
| Junction temperature | | Тj | 150 | °C | |
| Storage temperature range | | T _{stg} | -55 to 150 | °C | |

Absolute Maximum Ratings (Ta = 25°C)



Weight: 0.05 g (typ.)

Note 1: Mounted on an FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm²)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Industrial Applications

Unit: mm

Electrical Characteristics (Ta = 25°C)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------------|--------------|-----------------------|---|-----|------|------|------|
| Collector cut-off current | | I _{CBO} | $V_{CB}=40~V,~I_{E}=0$ | — | | 100 | nA |
| Emitter cut-off current | | I _{EBO} | $V_{EB} = 7 V, I_C = 0$ | _ | _ | 100 | nA |
| Collector-emitter breakdown voltage | | V (BR) CEO | $I_{C} = 10 \text{ mA}, I_{B} = 0$ | 20 | _ | _ | V |
| DC current gain | | h _{FE} (1) | $V_{CE} = 2 V, I_C = 0.5 A$ | 400 | _ | 1000 | |
| | | h _{FE} (2) | $V_{CE} = 2 V, I_C = 1.6 A$ | 200 | | | |
| Collector-emitter saturation voltage | | V _{CE (sat)} | $I_{C} = 1.6 \text{ A}, I_{B} = 32 \text{ mA}$ | _ | | 0.15 | V |
| Base-emitter saturation voltage | | V _{BE (sat)} | I _C = 1.6 A, I _B = 32 mA | _ | _ | 1.10 | V |
| Collector output capacitance | | C _{ob} | $V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$ | _ | 18 | _ | pF |
| Switching time | Rise time | tr | See Figure 1 circuit diagram. | _ | 100 | | ns |
| | Storage time | t _{stg} | $V_{CC} \simeq 12$ V, $R_L = 7.5 \Omega$ | _ | 350 | | |
| | Fall time | t _f | $I_{B1} = -I_{B2} = 53.3 \text{ mA}$ | _ | 90 | | |

Marking

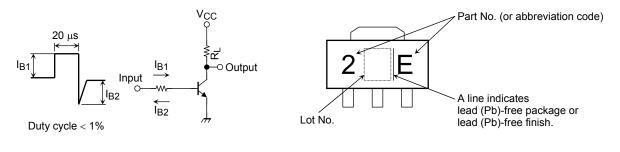
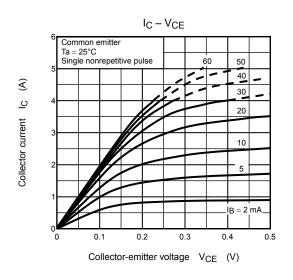
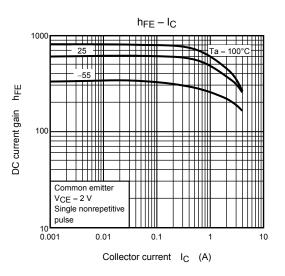
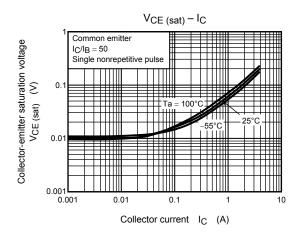


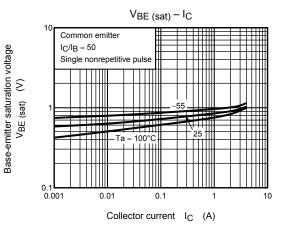
Figure 1 Switching Time Test Circuit & Timing Chart

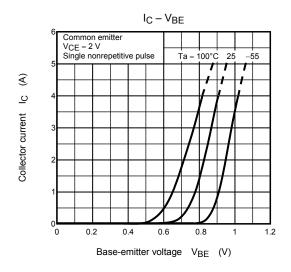
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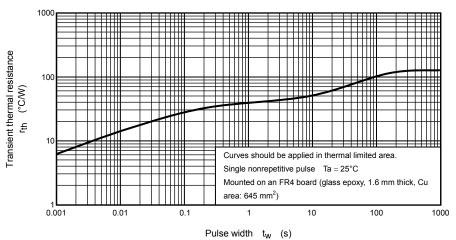




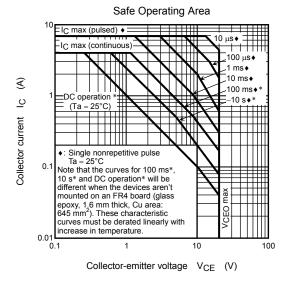








Transient Thermal Resistance rth - tw



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